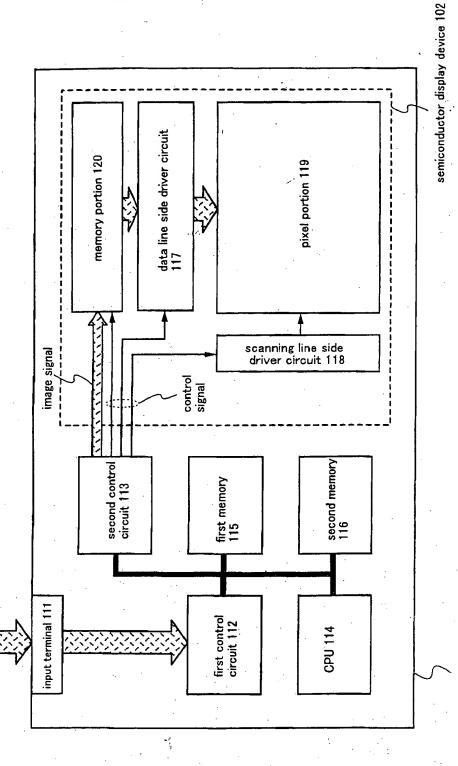
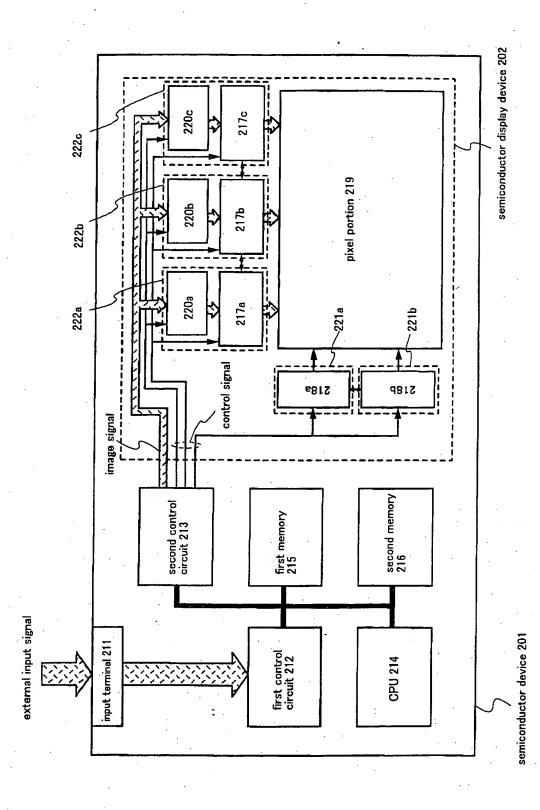
external input signal

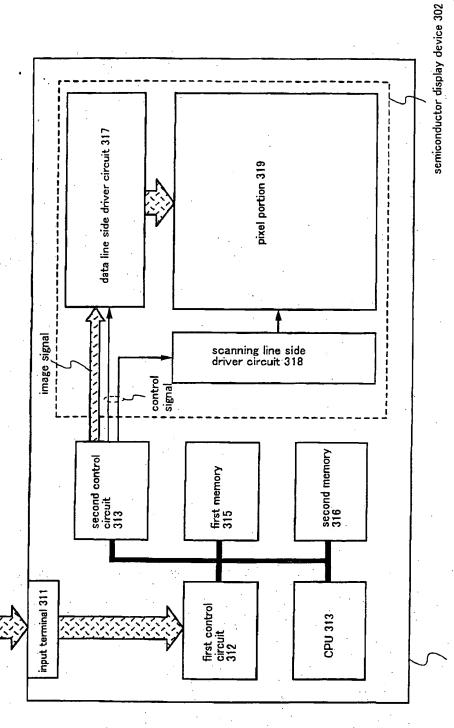


semiconductor device 101

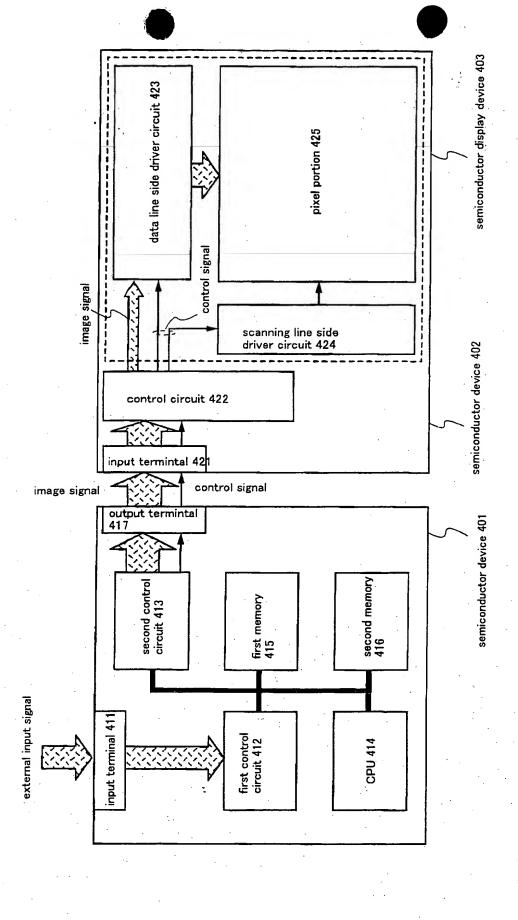


217a, 217b, 217c data line side driver circuit 218a, 218b scanning line side driver circuit 220a, 220b, 220c memory portion 221a, 221b scanning line side stick driver 222a, 222b, 222c data line side stick driver

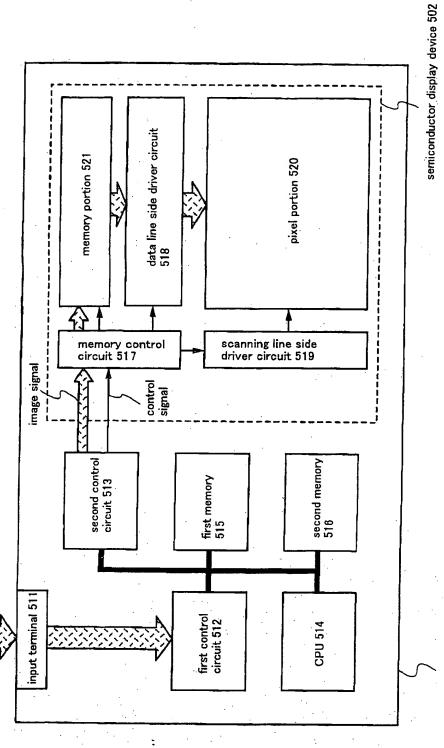
extermal input signal



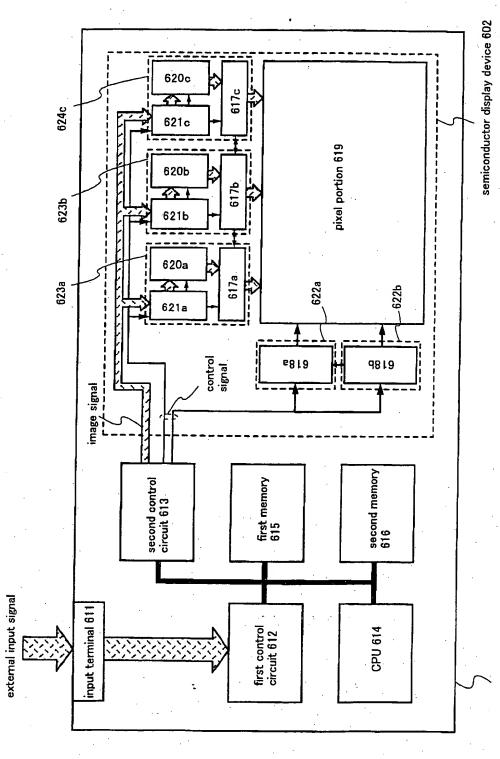
semiconductor device 301



external input signal

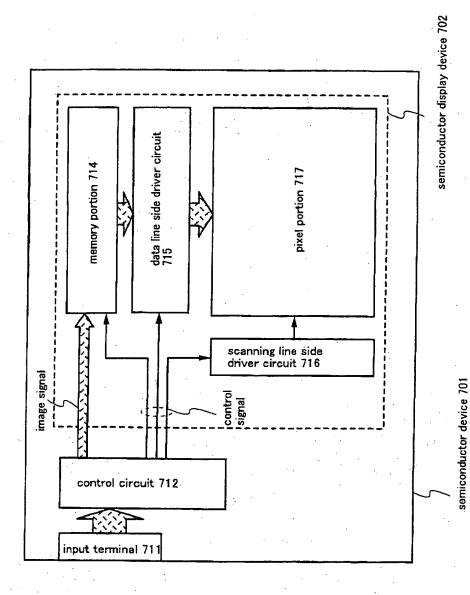


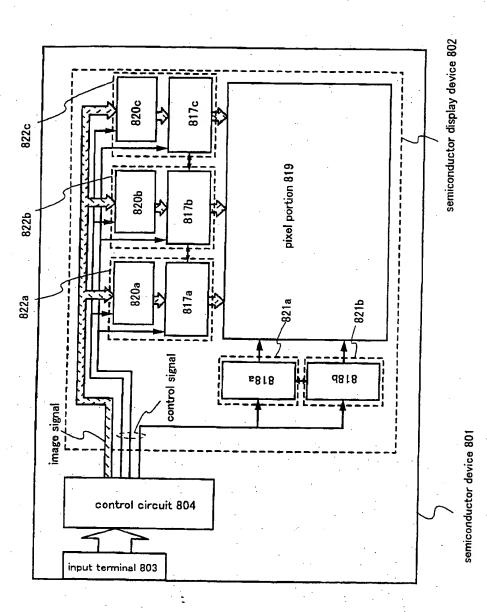
semiconductor device 501



semiconductor device 601

617a, 617b, 617c data line side driver circuit 618a, 618b scanning line side driver circuit 620a, 620b, 620c memory portion 621a, 621b, 621c memory control circuit 622a, 622b scanning line side stick driver 623a, 623b, 623c data line side stick driver





817a, 817b, 817c data line side driver circuit 818a, 818b scanning line side driver circuit 820a, 820b, 820c memory portion 821a, 821b scanning line side stick driver 822a, 822b, 822c data line side stick driver

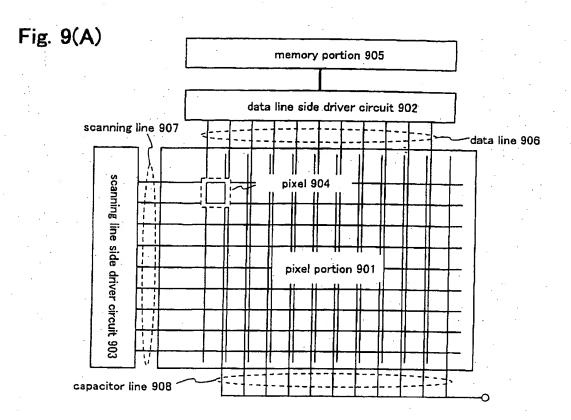
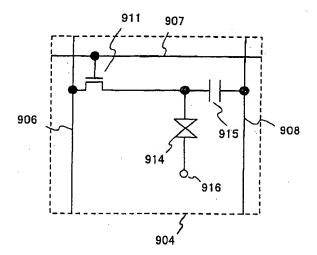


Fig. 9(B)



904 pixel 908 capacitor line 906 data line 907 scanning line 911 switching TFT 914 liquid crystal element 915 capacitor 916 counter electrode

Fig. 10 (A)

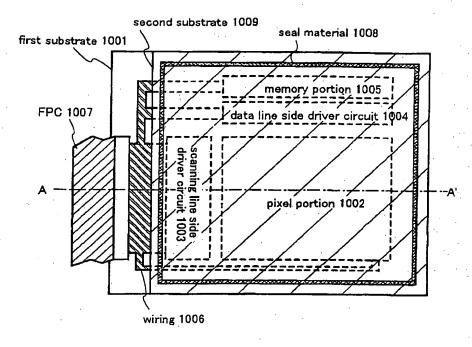


Fig. 10 (B)

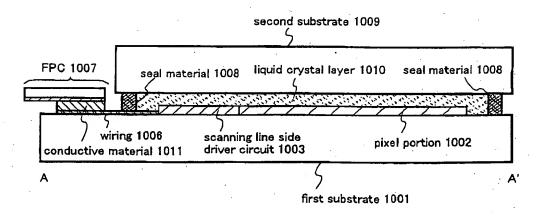
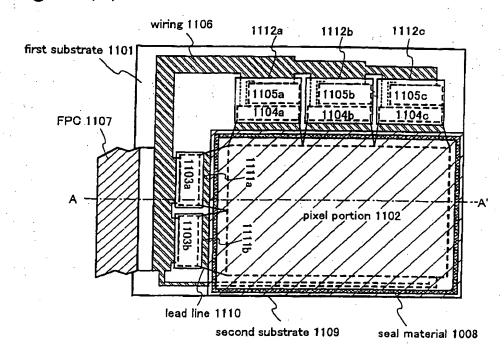
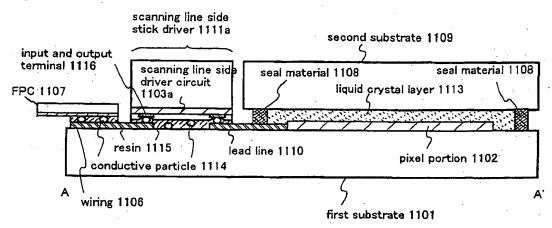


Fig. 11 (A)



1103a, 1103b scanning line side driver circuit 1104a, 1104b, 1104c data line side driver circuitc 1105a, 1105b, 1105c memory portion 1111a, 1111b scanning line side stick driver 1112a, 1112b, 1112c data line side stick driver

Fig. 11 (B)



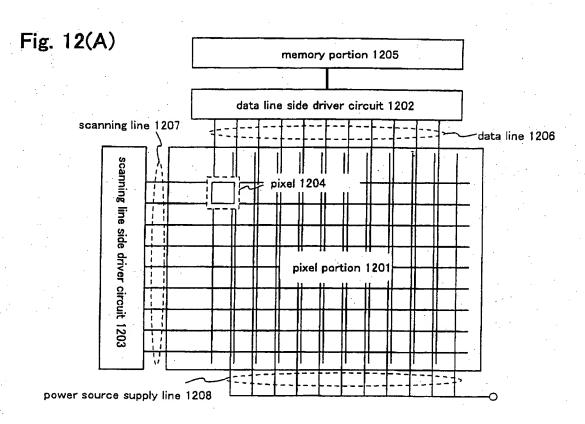
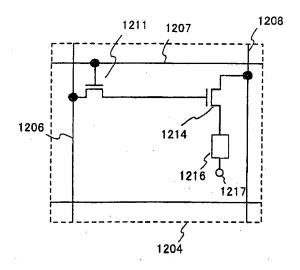


Fig. 12(B)



1204 pixel 1206 data line 1207 scanning line 1208 power source supply line 1211 switchin TFT 1214 EL driving TFT 1216 EL element 1217 counter electrode

Fig. 13(A)

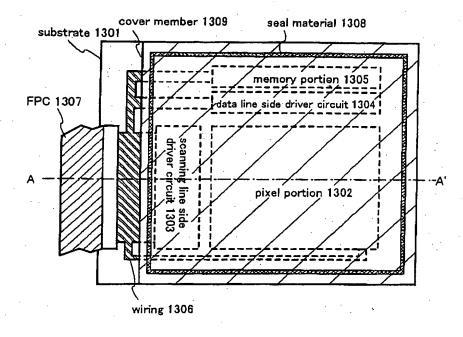


Fig. 13(B)

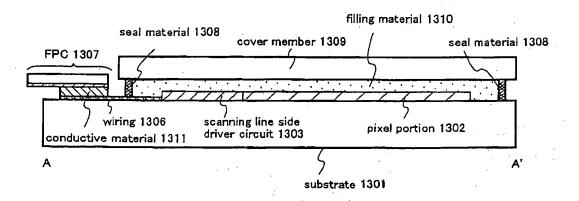
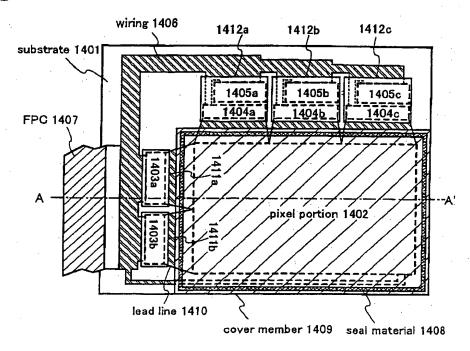
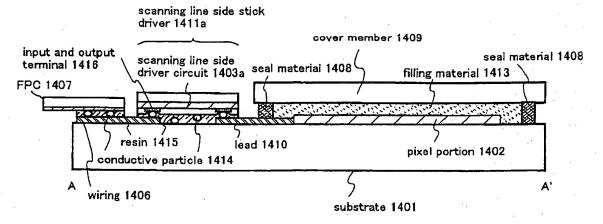


Fig. 14(A)



1403a, 1403b scanning line side driver circuit 1404a, 1404b, 1404c data line side driver circuit 1405a, 1405b, 1405c memory portion 1411a, 1411b scanning line side stick driver 1412a, 1412b, 1412c data line side stick driver

Fig. 14(B)



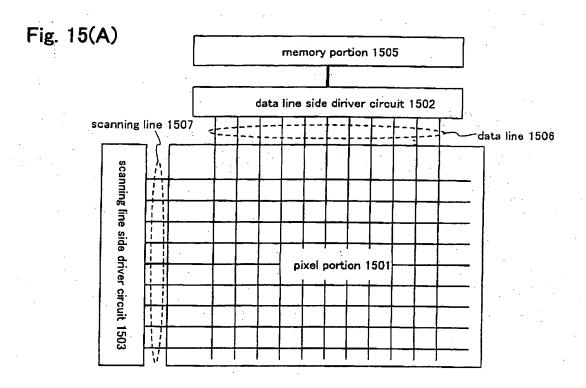
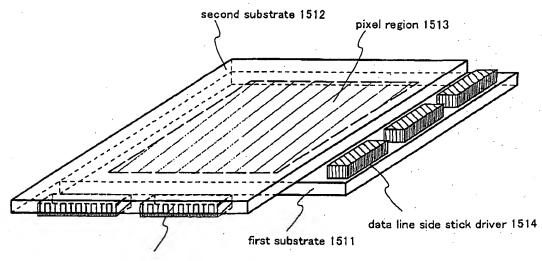


Fig. 15(B)



scanning line side sitick driver 1515

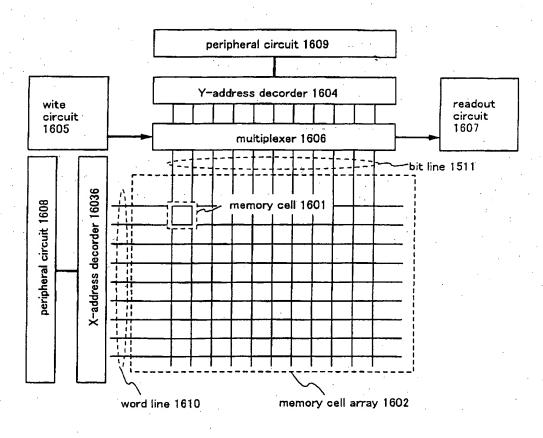


Fig. 17(A)

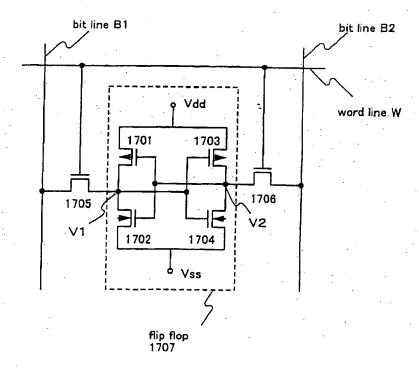
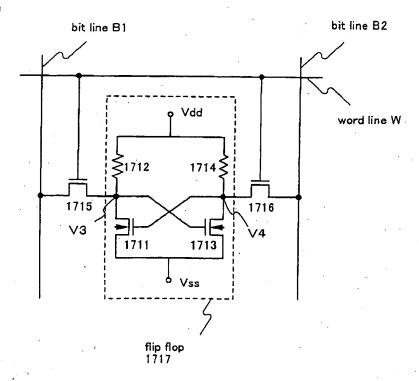
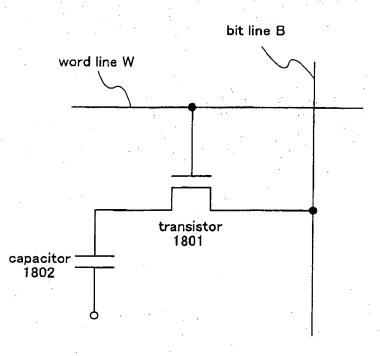


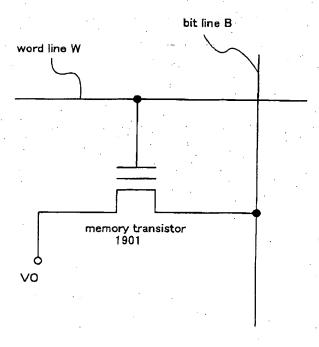
Fig. 17(B)

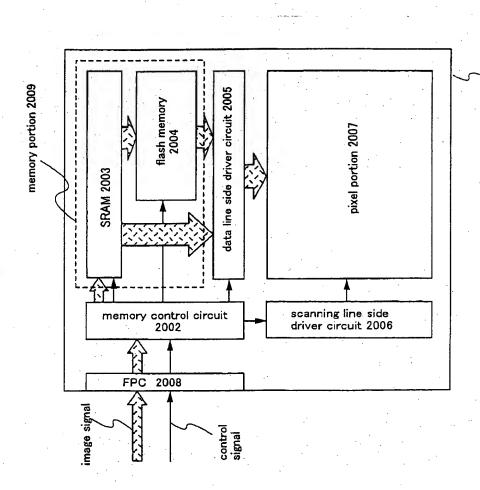






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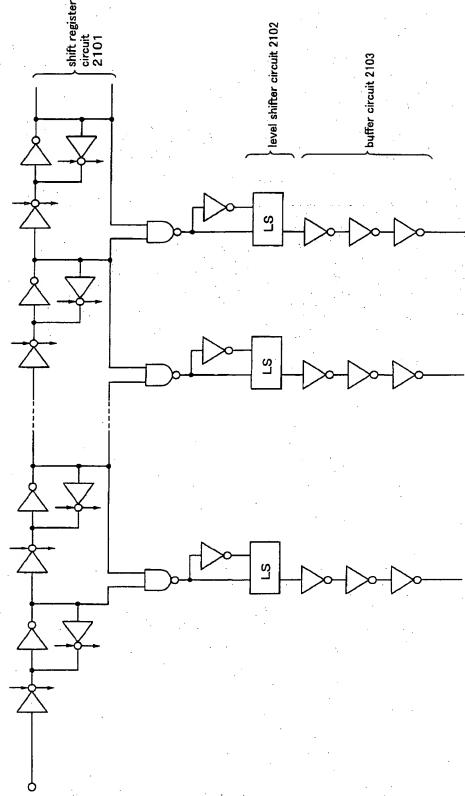




semiconductor display device 2001



[Fig. 21]



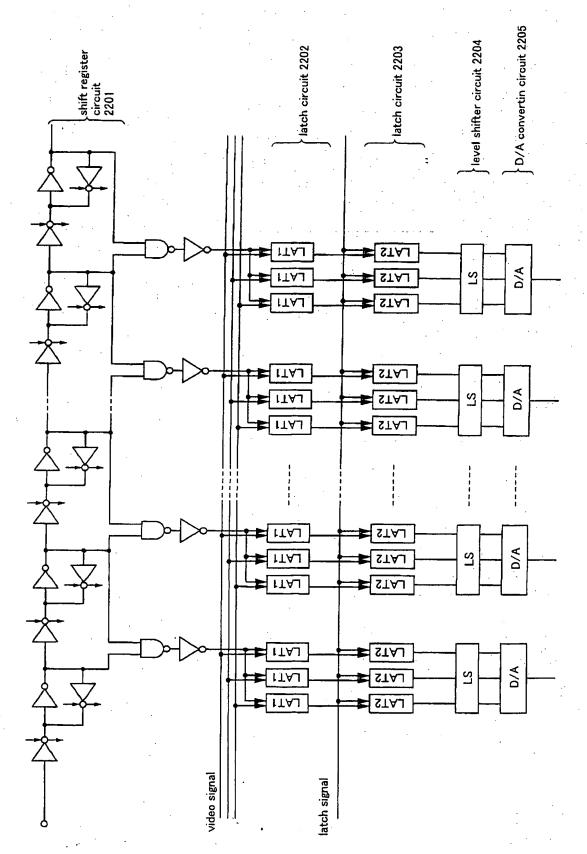
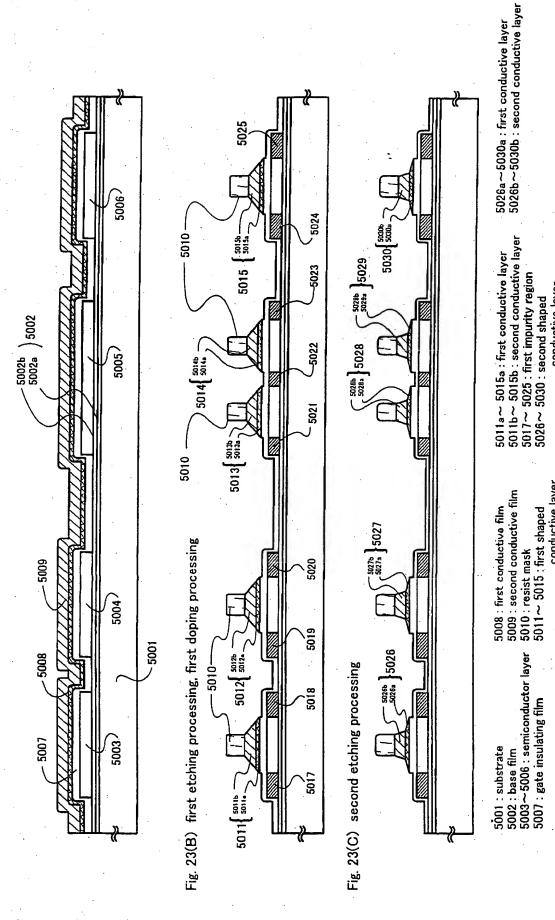


Fig. 22

Fig. 23(A) formation of island-like semiconductor layer, gate insulating film, and first and second conductive film for gate electrode



 $5011a \sim 5015a$: first conductive layer $5011b \sim 5015b$: second conductive layer $5017 \sim 5025$: first impurity region $5026 \sim 5030$: second shaped

5009: second conductive film 5010 : resist mask 5011~ 5015 : first shaped

conductive layer

conductive layer

Fig. 24(A) second doping processing

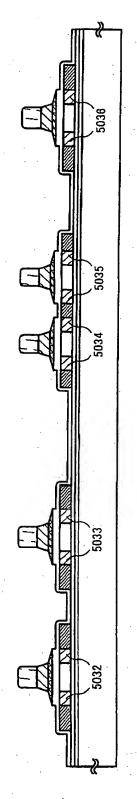


Fig. 24(B) third etching processing

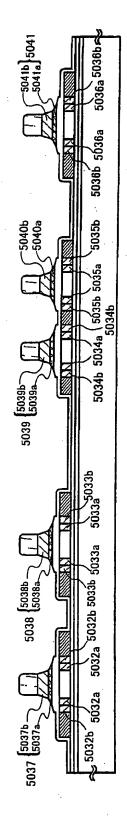
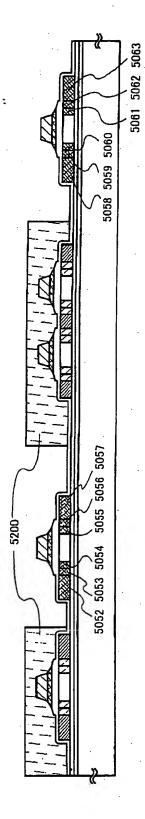


Fig. 24(C) third doping processing



5032~5036 : second impurity region 5032a~5036a : third impurity region 5032b~5036b : fourth impunity region

5037~5041 : third shaped conductive layer 5052~5063 : fifth impurity region 5200 : regist mask

formation of first, second interlayer insulating films and wiring formation

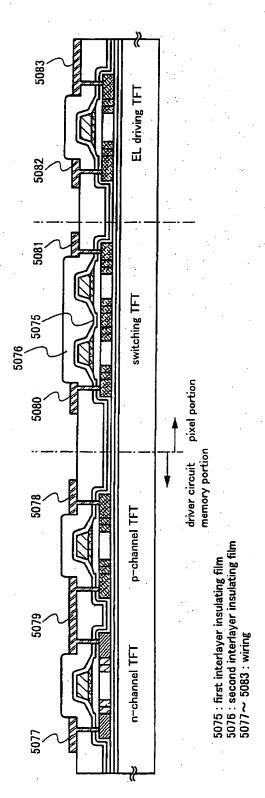
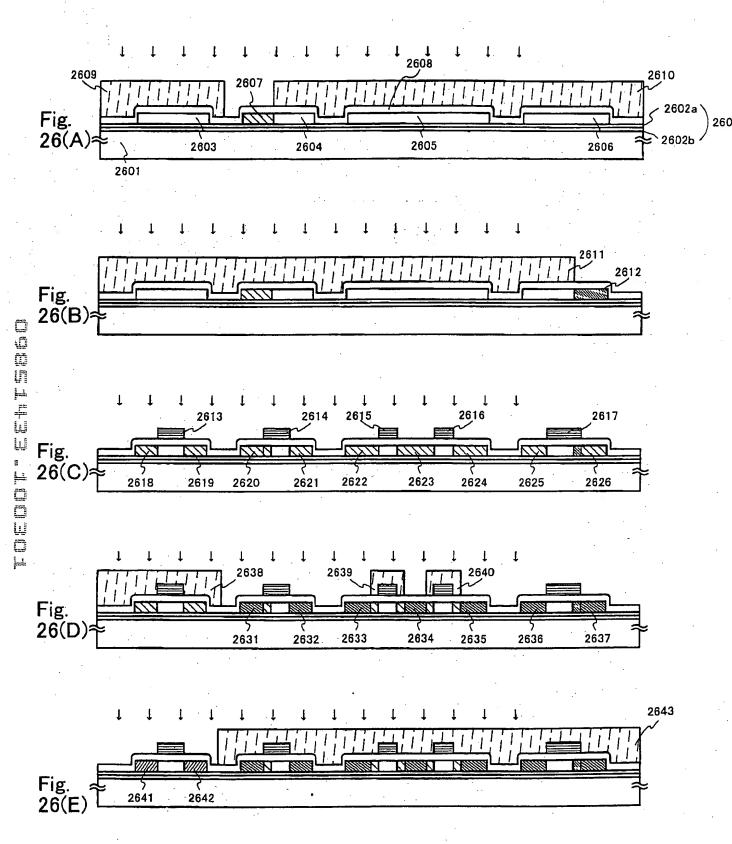


Fig. 25



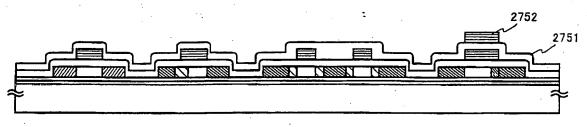


Fig.27(A)

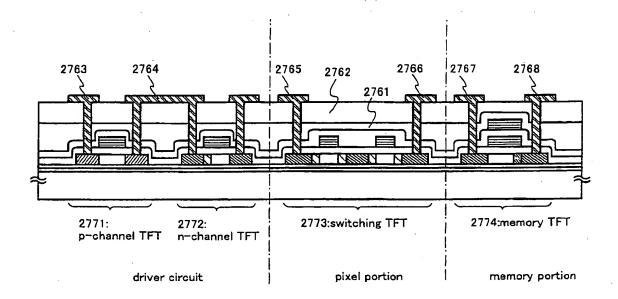
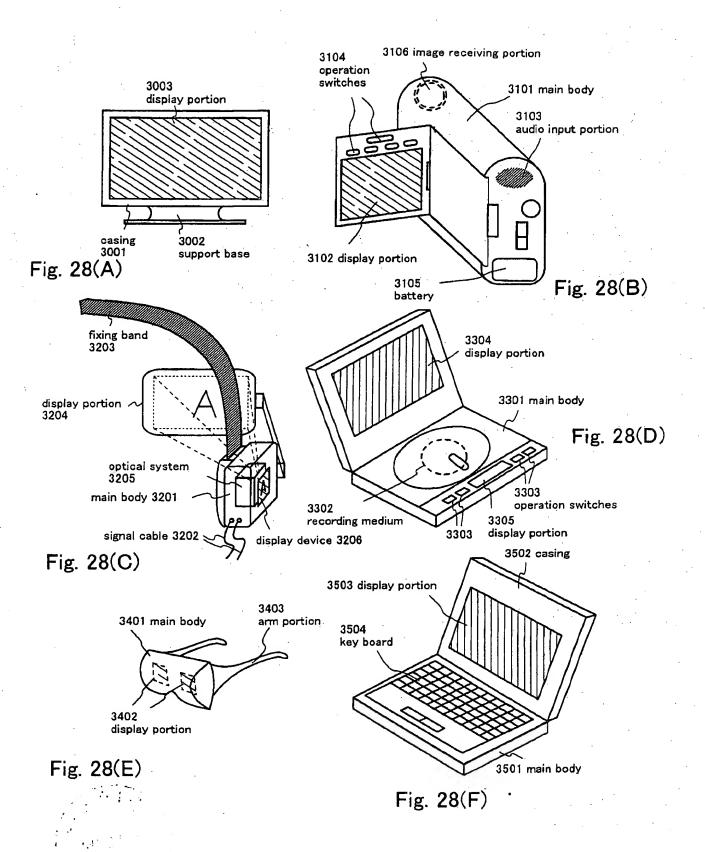


Fig.27(B)



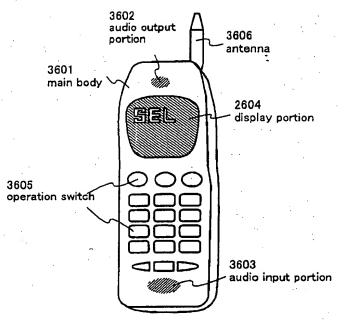


Fig. 29(A)

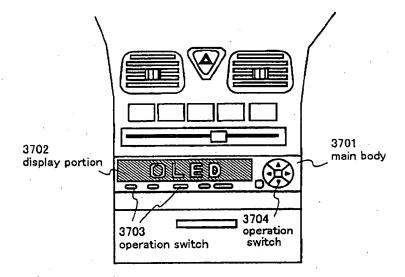


Fig. 29(B)